

PMPB23XNE

20 V, single N-channel Trench MOSFET 30 November 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 2.1 kV ESD protection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated, 100% solderable side pads for optical solder inspection

1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	10.1	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 7 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	19	22	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D I
2	D	drain	7	
3	G	gate		G T
4	S	source	3 8 4	
5	D	drain	Transparent top view	17
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa255
7	D	drain		
8	S	source		

Ordering information

Table 3. **Ordering information**

Type number	Package					
	Name	Description	Version			
PMPB23XNE	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

Marking

Table 4. Marking codes

Type number	Marking code
PMPB23XNE	1K

Limiting values 5.

Limiting values Table 5.

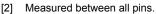
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	10.1	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	7	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	4.4	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	24	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.7	W
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	1.9	Α
ESD maximun	n rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	2100	V

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



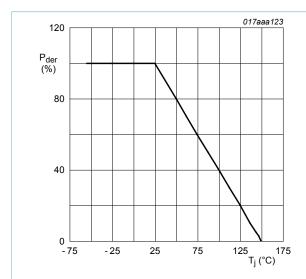


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

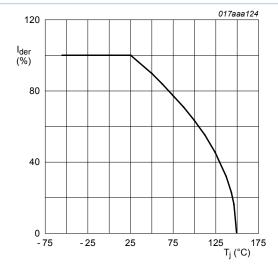


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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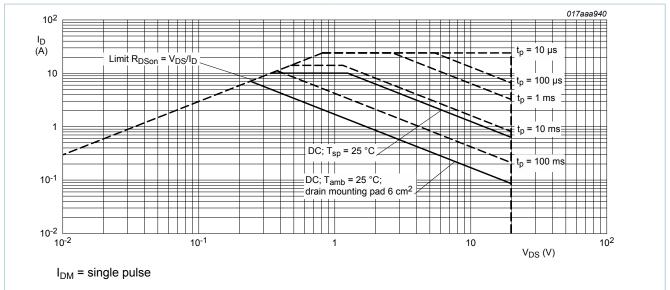


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient			[1]	-	235	270	K/W
	-		[2]	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	33	36	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			_	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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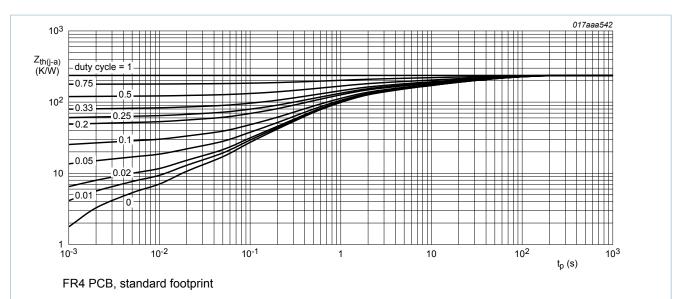


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

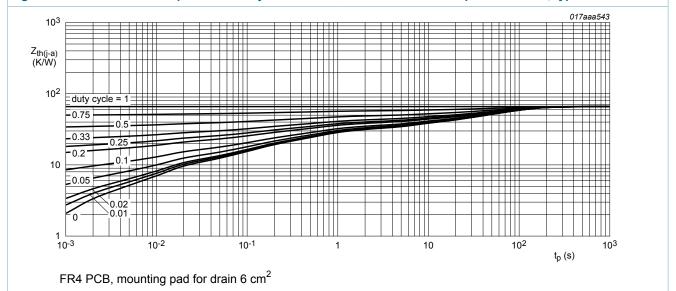


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 ^{\circ}C$		0.4	0.65	0.9	V
I _{DSS}	drain leakage current	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C		-	-	10	μA
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Symbol	Parameter	Conditions	N	/lin	Тур	Max	Unit
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-	-10	μA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 7 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	-	19	22	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 7 A; T _j = 150 °C	-	-	29	34	mΩ
		V_{GS} = 2.5 V; I_D = 6.1 A; T_j = 25 °C	-	-	23	29	mΩ
		V_{GS} = 1.8 V; I_{D} = 1.9 A; T_{j} = 25 °C	-	-	31	44	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 7 A; T _j = 25 °C	-	-	50	-	S
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	-	2.4	-	Ω
Dynamic cl	naracteristics				1		,
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 6 A; V_{GS} = 4.5 V; T_{j} = 25 °C	-	-	11.6	17	nC
Q_{GS}	gate-source charge		-	-	1.4	-	nC
Q_{GD}	gate-drain charge		-	-	2.2	-	nC
C _{iss}	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	-	1136	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	-	137	-	pF
C _{rss}	reverse transfer capacitance		-	-	112	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 10 \text{ V}; I_D = 6 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	-	9	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	-	20	-	ns
t _{d(off)}	turn-off delay time		-	-	31	-	ns
t _f	fall time		-	-	32	-	ns
Source-dra	in diode	,				1	
V _{SD}	source-drain voltage	$I_S = 1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	0.6	1.2	V

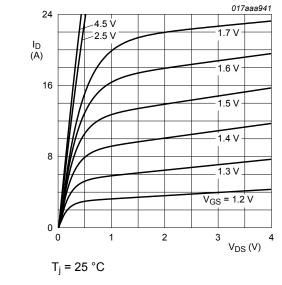


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

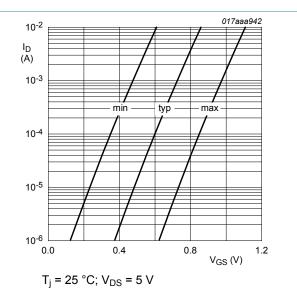


Fig. 7. Subthreshold drain current as a function of gate-source voltage

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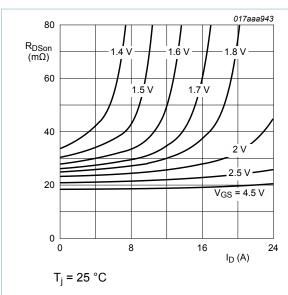


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

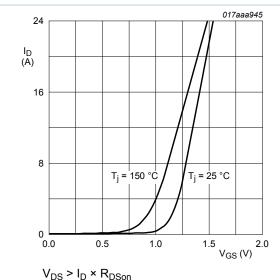


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

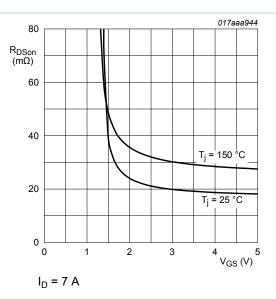


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

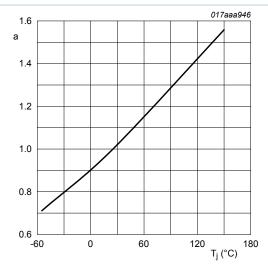


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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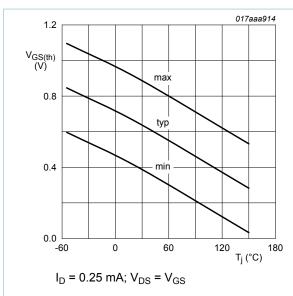


Fig. 12. Gate-source threshold voltage as a function of junction temperature

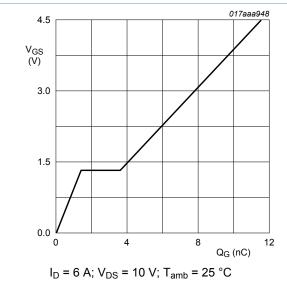


Fig. 14. Gate-source voltage as a function of gate charge; typical values

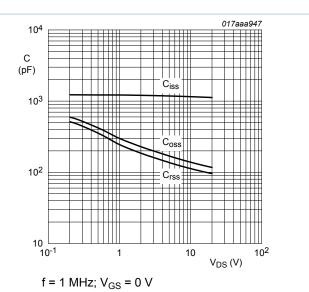


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

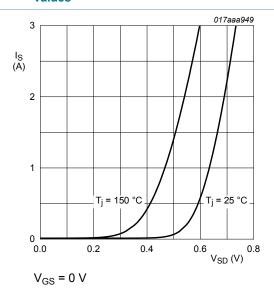
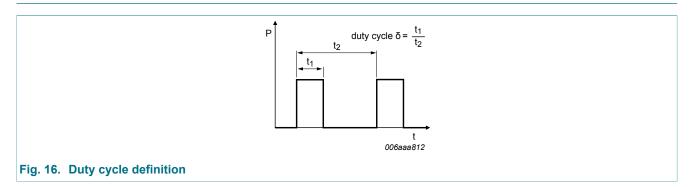


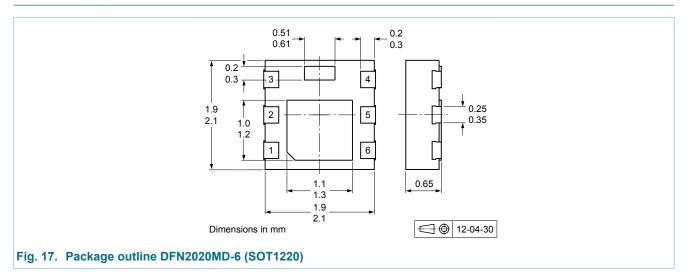
Fig. 15. Source current as a function of source-drain voltage; typical values

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8. Test information

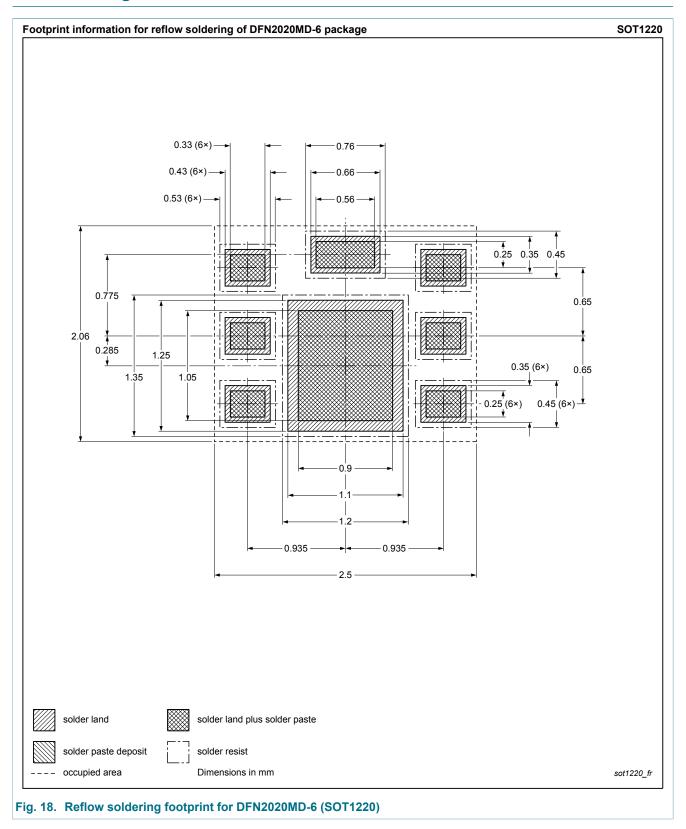


9. Package outline



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10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB23XNE v.1	20121130	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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